

**JIEJIE MICROELECTRONICS CO., LTD**

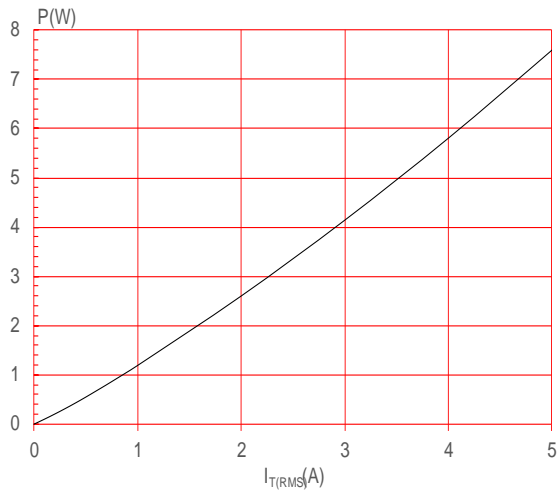
Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	3.5	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25$  unless otherwise specified)

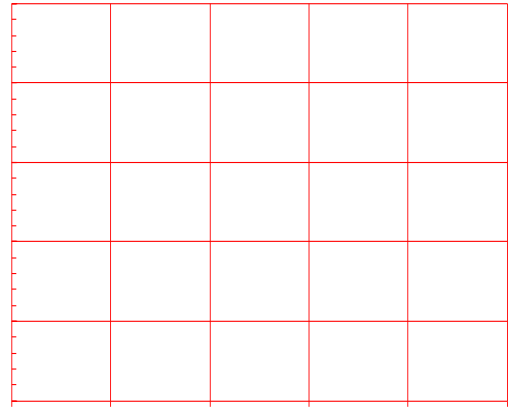
Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V$ $R_L=33$	- -	MAX.	25	mA
$V_{GT}$		- -	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	40	mA <sup>40</sup>



**FIG.1:** Maximum power dissipation versus RMS on-state current



**FIG.2:** RMS on-state current versus case temperature



**ACJT425-10A**



**PACKAGE MECHANICAL DATA**

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